

Amendments to the Specification

Please replace the paragraph [0125] beginning at page 30, with the following rewritten paragraph:

[0125] FIG. 13 is a chart showing the driving timing of the charge pump circuit 80a.

First, the charge charged to the capacitors C83 and C84 is discharged by the start pulse HST. Then, by turning on the transistor Q81 by the driving pulse H2, the power supply voltage VDD is charged to the capacitor C82 and the potentials of the capacitors C81 and C82 are boosted by the driving pulses H1 and H2, thereby generating a boosting voltage higher than the power supply voltage VDD in a short time.

Please replace the paragraph [0152] beginning at page 38, with the following rewritten paragraph:

[0152] A solid state image pickup device 240 according to the seventh embodiment of the present invention is different from the solid state image pickup devices 210, ~~2-220~~ and ~~3-230~~ of the fourth to third embodiments in that an impedance conversion circuit 51 is added to an input unit of the signal output unit 50a.

Please replace the paragraph [0153] beginning at page 38, with the following rewritten paragraph:

[0153] According to the solid state image pickup device 240 of the seventh embodiment, since the signal from the noise cancellation unit 40 is transferred to the horizontal signal line Lm through the impedance conversion circuit 51 that impedance-converts the signal first of all, the capacitance distribution due to the horizontal signal line parasitic capacitor C51 does not occur, so that higher sensitivity and lower noise than the above-described solid state image pickup devices 210, ~~2-220~~ and ~~3-230~~ can be realized and reduction in chip area can be easily realized.